

ADG428/ADG429—SPECIFICATIONS

DUAL SUPPLY¹ ($V_{DD} = +15\text{ V}$, $V_{SS} = -15\text{ V}$, $GND = 0\text{ V}$, $\overline{WR} = 0\text{ V}$, $\overline{RS} = 2.4\text{ V}$ unless otherwise noted)

Parameter	B Version -40°C to +25°C	T Version -55°C to +25°C	Units	Test Conditions/Comments
ANALOG SWITCH				
Analog Signal Range	V _{SS} to V _{DD}	V _{SS} to V _{DD}	V	
R _{ON}	60 100 10	125 100 10	Ω typ Ω max % max	V _D = ±10 V, I _S = -1 mA -10 V < V _S < 10 V, I _S = -1 mA
ΔR _{ON}				
LEAKAGE CURRENTS				
Source OFF Leakage I _S (OFF)	±0.03 ±0.3 ±0.5 ±50	±0.03 ±0.3 ±0.5 ±50	nA typ nA max	V _D = ±10 V, V _S = ±10 V; Test Circuit 2
Drain OFF Leakage I _D (OFF) ADG428	±0.07 ±0.7 ±1 ±100	±0.07 ±0.7 ±1 ±100	nA typ nA max	V _D = ±10 V, V _S = ±10 V; Test Circuit 3
ADG429	±0.05 ±0.5 ±1 ±50	±0.05 ±0.5 ±1 ±50	nA typ nA max	
Channel ON Leakage I _D , I _S (ON) ADG428 ADG429	±1 ±100 ±1 ±50	±1 ±100 ±1 ±50	nA max nA max	V _S = V _D = ±10 V; Test Circuit 4
DIGITAL INPUTS				
Input High Voltage, V _{INH}	2.4	2.4	V min	
Input Low Voltage, V _{INL}	0.8	0.8	V max	
Input Current I _{INL} or I _{INH}	±0.1 ±1	±0.1 ±1	μA max	
C _{IN} , Digital Input Capacitance	8	8	pF typ	V _{IN} = 0 or V _{DD} f = 1 MHz
DYNAMIC CHARACTERISTICS ²				
t _{TRANSITION}	110 250	300	ns typ ns max	R _L = 1 MΩ, C _L = 35 pF; V _{SI} = ±10 V, V _{SS} = ±10 V; Test Circuit 5
t _{OPEN}		10	ns min	R _L = 1 kΩ, C _L = 35 pF; V _S = +5 V; Test Circuit 6
t _{ON} (EN, \overline{WR})	115 150	225	ns typ ns max	R _L = 1 kΩ, C _L = 35 pF; V _S = +5 V; Test Circuit 7
t _{OFF} (EN, \overline{RS})	105 150	300	ns typ ns max	R _L = 1 kΩ, C _L = 35 pF; V _S = +5 V; Test Circuit 7
t _W , Write Pulsewidth	100	100	ns min	
t _S , Address, Enable Setup Time	100	100	ns min	
t _H , Address, Enable Hold Time	10	10	ns min	
t _{RS} , Reset Pulsewidth	100	100	ns min	
Charge Injection	4	4	pC typ	V _S = +5 V V _S = 0 V, R _S = 0 Ω, C _L = 10 nF; Test Circuit 10
OFF Isolation	-75 -60	-75 -60	dB typ dB min	R _L = 1 kΩ, C _L = 15 pF, f = 100 kHz; V _S = 7 V rms, V _{EN} = 0 V; Test Circuit 11
Channel-to-Channel Crosstalk	85	85	dB typ	R _L = 1 kΩ, C _L = 15 pF, f = 100 kHz; Test Circuit 12
C _S (OFF)	11	11	pF typ	f = 1 MHz
C _D (OFF) ADG428	40	40	pF typ	f = 1 MHz
ADG429	20	20	pF typ	
C _D , C _S (ON) ADG428	54	54	pF typ	
ADG429	34	34	pF typ	f = 1 MHz
POWER REQUIREMENTS				
I _{DD}	20 100	20 100	μA typ μA max	V _{IN} = 0 V, V _{EN} = 0 V
I _{SS}	0.001 5	0.001 5	μA typ μA max	

NOTES

¹Temperature ranges are as follows: B Version: -40°C to +85°C; T Version: -55°C to +125°C.

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

SINGLE SUPPLY¹ ($V_{DD} = +12\text{ V}$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, $\overline{WR} = 0\text{ V}$, $\overline{RS} = 2.4\text{ V}$ unless otherwise noted)

Parameter	B Version -40°C to +25°C		T Version -55°C to +25°C		Units	Test Conditions/Comments
ANALOG SWITCH						
Analog Signal Range	0 to V_{DD}		0 to V_{DD}		V	
R_{ON}	90	200	90	200	Ω typ	$V_D = +10\text{ V}$, $I_S = -500\text{ }\mu\text{A}$
ΔR_{ON}	10		10		Ω max % max	$0\text{ V} < V_S < 10\text{ V}$, $I_S = -1\text{ mA}$
LEAKAGE CURRENTS						
Source OFF Leakage I_S (OFF)	± 0.005	± 0.005	± 0.005	± 0.005	nA typ	$V_D = 10\text{ V}/0\text{ V}$, $V_S = 0\text{ V}/10\text{ V}$;
	± 0.5	± 50	± 0.5	± 50	nA max	Test Circuit 2
Drain OFF Leakage I_D (OFF)	± 0.015	± 0.015	± 0.015	± 0.015	nA typ	$V_D = 10\text{ V}/0\text{ V}$, $V_S = 0\text{ V}/10\text{ V}$;
ADG428	± 1	± 100	± 1	± 100	nA max	Test Circuit 3
ADG429	± 0.008	± 0.008	± 0.008	± 0.008	nA typ	
Channel ON Leakage I_D , I_S (ON)	± 1	± 50	± 1	± 50	nA max	
ADG428	± 0.02	± 0.02	± 0.02	± 0.02	nA typ	$V_S = V_D = 10\text{ V}/0\text{ V}$;
ADG429	± 1	± 100	± 1	± 100	nA max	Test Circuit 4
± 0.01	± 50	± 0.01	± 50	± 50	nA max	
± 1		± 1	± 50	± 50	nA max	
DIGITAL INPUTS						
Input High Voltage, V_{INH}	2.4		2.4		V min	
Input Low Voltage, V_{INL}	0.8		0.8		V max	
Input Current						
I_{INL} or I_{INH}	± 1		± 1		μA max	$V_{IN} = 0$ or V_{DD}
C_{IN} , Digital Input Capacitance	8		8		pF typ	$f = 1\text{ MHz}$
DYNAMIC CHARACTERISTICS ²						
$t_{TRANSITION}$	250	250	250	250	ns typ	$R_L = 1\text{ M}\Omega$, $C_L = 35\text{ pF}$;
	350	450	350	450	ns max	$V_{S1} = 10\text{ V}/0\text{ V}$, $V_{SS} = 0\text{ V}/10\text{ V}$;
						Test Circuit 5
t_{OPEN}	25	10	25	10	ns min	$R_L = 1\text{ k}\Omega$, $C_L = 35\text{ pF}$;
						$V_S = +5\text{ V}$; Test Circuit 6
t_{ON} (EN, \overline{WR})	200	200	200	200	ns typ	$R_L = 1\text{ k}\Omega$, $C_L = 35\text{ pF}$;
	300	400	300	400	ns max	$V_S = +5\text{ V}$; Test Circuit 7
t_{OFF} (EN, \overline{RS})	80	80	80	80	ns typ	$R_L = 1\text{ k}\Omega$, $C_L = 35\text{ pF}$;
	300	400	300	400	ns max	$V_S = +5\text{ V}$; Test Circuit 7
t_W , Write Pulsewidth	100		100		ns min	
t_S , Address, Enable Setup Time	100		100		ns min	
t_H , Address, Enable Hold Time	10		10		ns min	
t_{RS} , Reset Pulswidth	100		100		ns min	
Charge Injection	4		4		pC typ	
OFF Isolation	-75	-75	-75	-75	dB typ	$R_L = 1\text{ k}\Omega$, $C_L = 15\text{ pF}$, $f = 100\text{ kHz}$;
	-60	-60	-60	-60	dB min	$V_S = 7\text{ V rms}$, $V_{EN} = 0\text{ V}$; Test Circuit 11
Channel-to-Channel Crosstalk	85	85	85	85	dB typ	$R_L = 1\text{ k}\Omega$, $C_L = 15\text{ pF}$, $f = 100\text{ kHz}$;
						Test Circuit 12
C_S (OFF)	11		11		pF typ	
C_D (OFF)						
ADG428	40		40		pF typ	$f = 1\text{ MHz}$
ADG429	20		20		pF typ	$f = 1\text{ MHz}$
C_D , C_S (ON)						
ADG428	54		54		pF typ	$f = 1\text{ MHz}$
ADG429	34		34		pF typ	
POWER REQUIREMENTS						
I_{DD}	20		20		μA typ	$V_{IN} = 0\text{ V}$, $V_{EN} = 0\text{ V}$
	100		100		μA max	

NOTES

¹Temperature ranges are as follows: B Version: -40°C to +85°C; T Version: -55°C to +125°C.²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ADG428/ADG429

ABSOLUTE MAXIMUM RATINGS¹

(T_A = +25°C unless otherwise noted.)

V _{DD} to V _{SS}	+44 V
V _{DD} to GND	-0.3 V to +25 V
V _{SS} to GND	+0.3 V to -25 V
Analog, Digital Inputs ²	V _{SS} - 2 V to V _{DD} + 2 V or 30 mA, Whichever Occurs First
Continuous Current, S or D	30 mA
Peak Current, S or D	100 mA (Pulsed at 1 ms, 10% Duty Cycle Max)
Operating Temperature Range	
Industrial (B Version)	-40°C to +85°C
Extended (T Version)	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature	+150°C
Cerdip Package, Power Dissipation	900 mW
θ _{JA} , Thermal Impedance	73°C/W
Lead Temperature, Soldering (10 sec)	+300°C
Plastic Package, Power Dissipation	470 mW
θ _{JA} , Thermal Impedance	115°C/W
Lead Temperature, Soldering (10 sec)	+260°C
SOIC Package, Power Dissipation	600 mW
θ _{JA} , Thermal Impedance	77°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	+215°C
PLCC Package, Power Dissipation	800 mW
θ _{JA} , Thermal Impedance	90°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	+215°C
Infrared (15 sec)	+220°C

NOTES

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

²Overvoltages at A, EN, WR, RS, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

ORDERING GUIDE

Model ¹	Temperature Range	Package Options ²
ADG428BN	-40°C to +85°C	N-18
ADG428BP	-40°C to +85°C	P-20A
ADG428BR	-40°C to +85°C	R-18
ADG428TQ	-55°C to +125°C	Q-18
ADG429BN	-40°C to +85°C	N-18
ADG429BP	-40°C to +85°C	P-20A
ADG429TQ	-55°C to +125°C	Q-18

NOTES

¹For availability of MIL-STD-883, Class B processed parts, contact factory.

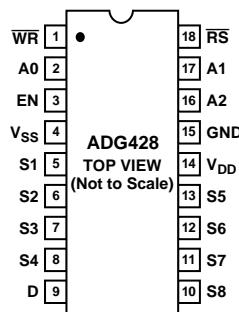
²N = Plastic DIP; P = Plastic Leaded Chip Carrier (PLCC); Q = Cerdip;
R = Small Outline IC (SOIC).

CAUTION

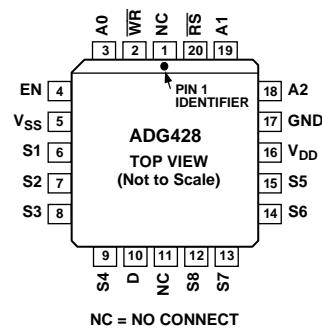
ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG428/ADG429 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

ADG428 PIN CONFIGURATIONS

DIP/SOIC

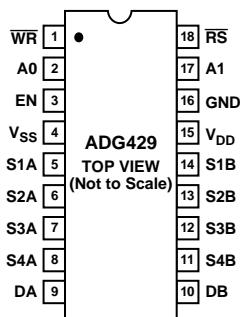


PLCC

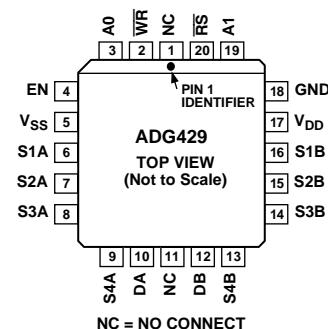


ADG429 PIN CONFIGURATIONS

DIP



PLCC



WARNING!



TERMINOLOGY

V_{DD}	Most positive power supply potential.
V_{SS}	Most negative power supply potential in dual supplies. In single supply applications, it may be connected to ground.
GND	Ground (0 V) reference.
R_{ON}	Ohmic resistance between D and S.
ΔR_{ON}	Difference between the R_{ON} of any two channels.
I_S (OFF)	Source leakage current when the switch is off.
I_D (OFF)	Drain leakage current when the switch is off.
I_D, I_S (ON)	Channel leakage current when the switch is on.
V_D (V_S)	Analog voltage on terminals D, S.
C_S (OFF)	Channel input capacitance for “OFF” condition.
C_D (OFF)	Channel output capacitance for “OFF” condition.
C_D, C_S (ON)	“ON” switch capacitance.
C_{IN}	Digital input capacitance.
t_{ON} (EN)	Delay time between the 50% and 90% points of the digital input and switch “ON” condition.
t_{OFF} (EN)	Delay time between the 50% and 90% points of the digital input and switch “OFF” condition.
$t_{TRANSITION}$	Delay time between the 50% and 90% points of the digital inputs and the switch “ON” condition when switching from one address state to another.
t_{OPEN}	“OFF” time measured between 80% points of both switches when switching from one address state to another.
V_{INL}	Maximum input voltage for Logic “0.”
V_{INH}	Minimum input voltage for Logic “1.”
I_{INL} (I_{INH})	Input current of the digital input.
Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation	A measure of unwanted signal coupling through an “OFF” channel.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
I_{DD}	Positive supply current.
I_{SS}	Negative supply current.

ADG428 Truth Table

A2	A1	A0	EN	WR	RS	ON SWITCH
Latching						
X	X	X	X	1	1	Maintains Previous Switch Condition
Reset						
X	X	X	X	X	0	NONE (Latches Cleared)
Transparent Operation						
X	X	X	0	0	1	NONE
0	0	0	1	0	1	1
0	0	1	1	0	1	2
0	1	0	1	0	1	3
0	1	1	1	0	1	4
1	0	0	1	0	1	5
1	0	1	1	0	1	6
1	1	0	1	0	1	7
1	1	1	1	0	1	8

ADG429 Truth Table

A1	A0	EN	WR	RS	ON SWITCH PAIR
Latching					
X	X	X	1	1	Maintains Previous Switch Condition
Reset					
X	X	X	X	0	NONE (Latches Cleared)
Transparent Operation					
X	X	0	0	1	NONE
0	0	1	0	1	1
0	1	1	0	1	2
1	0	1	0	1	3
1	1	1	0	1	4

ADG428/ADG429

TIMING DIAGRAMS

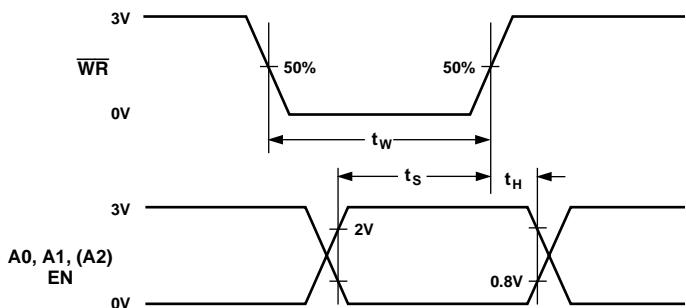


Figure 1.

Figure 1 shows the timing sequence for latching the switch address and enable inputs. The latches are level sensitive; therefore, while \overline{WR} is held low, the latches are transparent and the switches respond to the address and enable inputs. This input data is latched on the rising edge of \overline{WR} .

Typical Characteristics

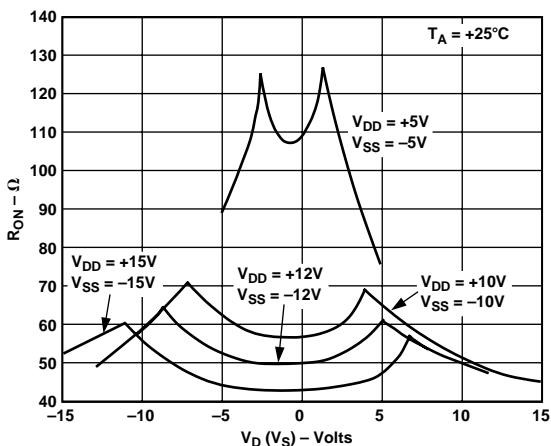


Figure 3. R_{ON} as a Function of V_D (V_S): Dual Supply Voltage

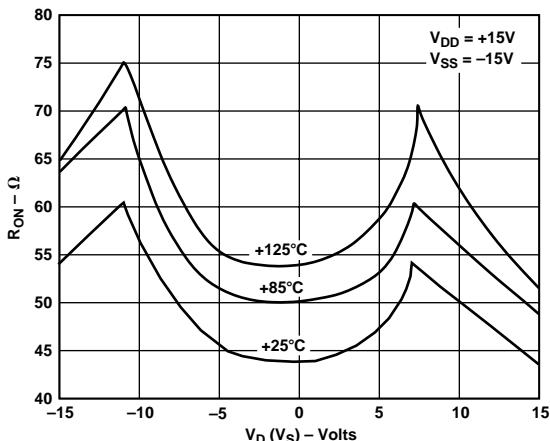


Figure 4. R_{ON} as a Function of V_D (V_S) for Different Temperatures

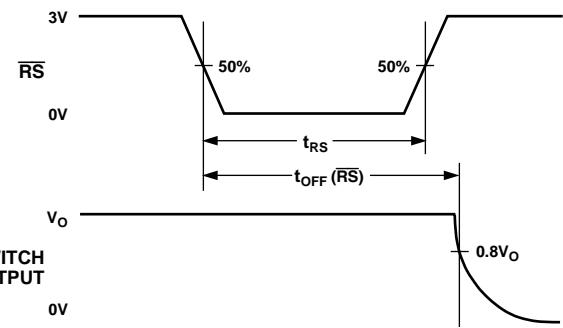


Figure 2.

Figure 2 shows the Reset Pulsewidth, t_{RS} , and the Reset Turnoff Time, t_{OFF} , (\overline{RS}).

Note: All digital input signals rise and fall times are measured from 10% to 90% of 3 V. $t_r = t_f = 20$ ns.

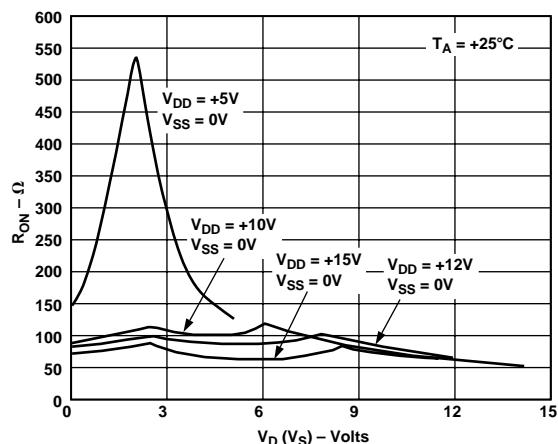


Figure 5. R_{ON} as a Function of V_D (V_S): Single Supply Voltage

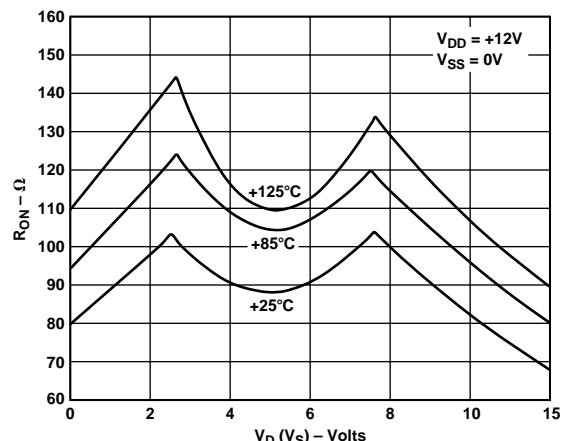


Figure 6. R_{ON} as a Function of V_D (V_S) for Different Temperatures

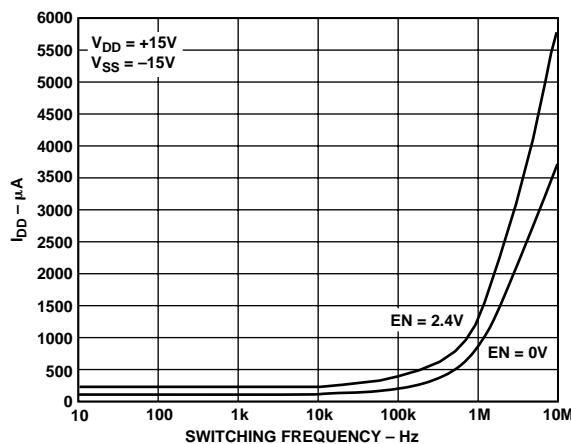


Figure 7. Positive Supply Current vs. Switching Frequency

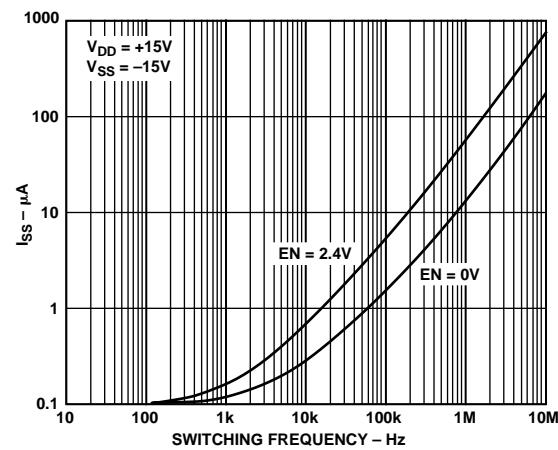


Figure 10. Negative Supply Current vs. Switching Frequency

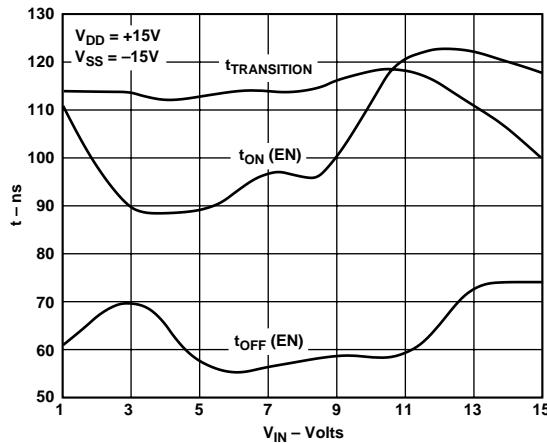


Figure 8. Switching Time vs. V_{IN} (Bipolar Supply)

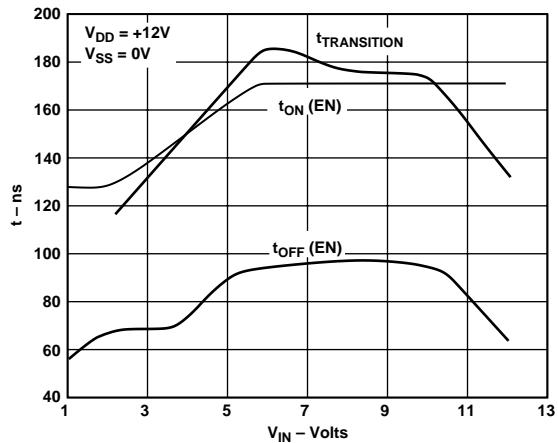


Figure 11. Switching Time vs. V_{IN} (Single Supply)

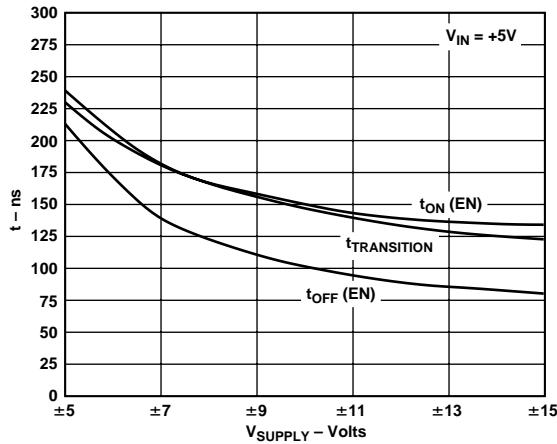


Figure 9. Switching Time vs. Bipolar Supply

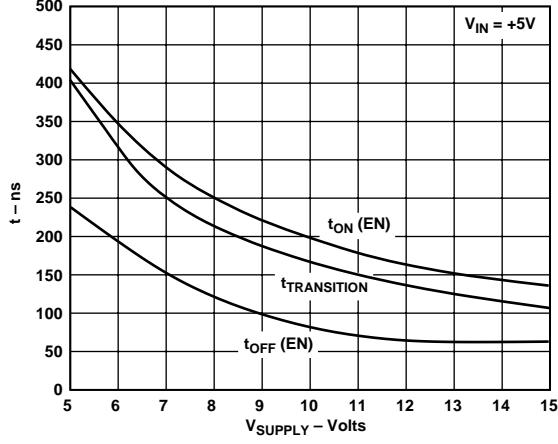


Figure 12. Switching Time vs. Single Supply

ADG428/ADG429

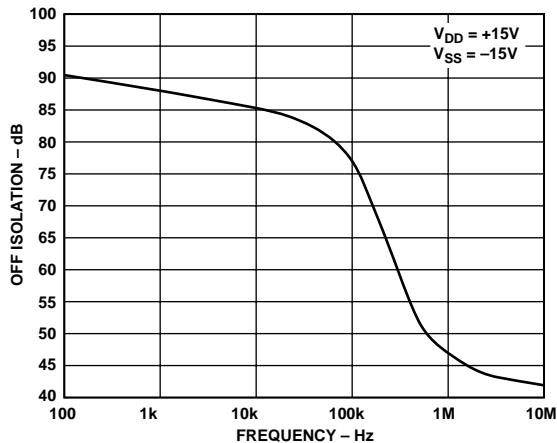


Figure 13. OFF Isolation vs. Frequency

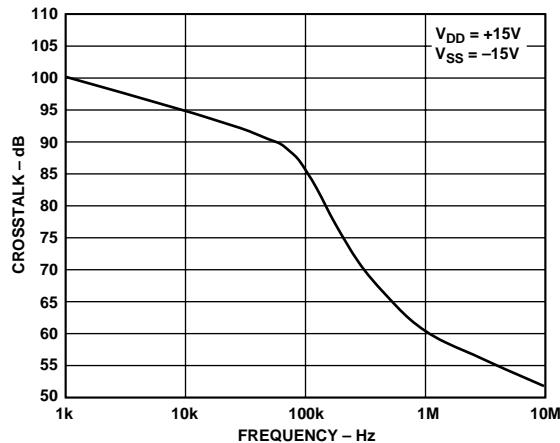


Figure 15. Crosstalk vs. Frequency

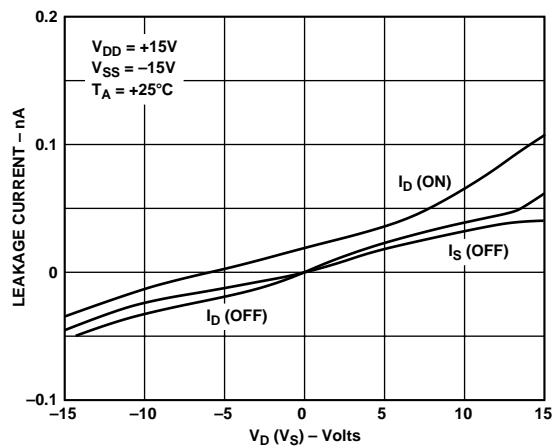


Figure 14. Leakage Currents as a Function of V_D (V_S)

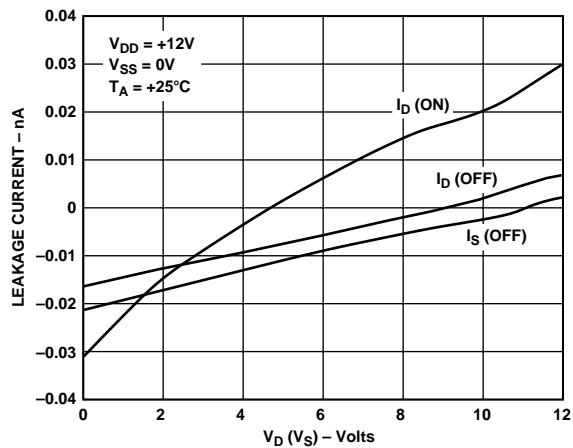
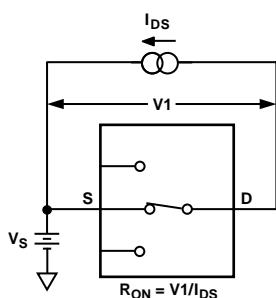
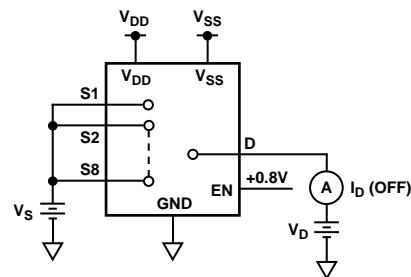
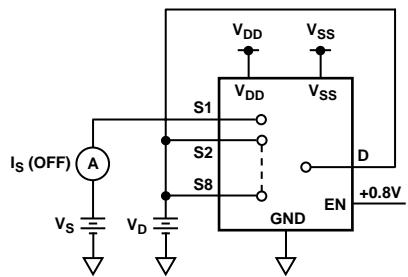
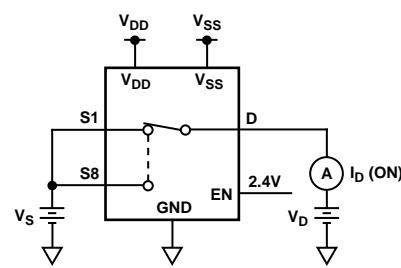
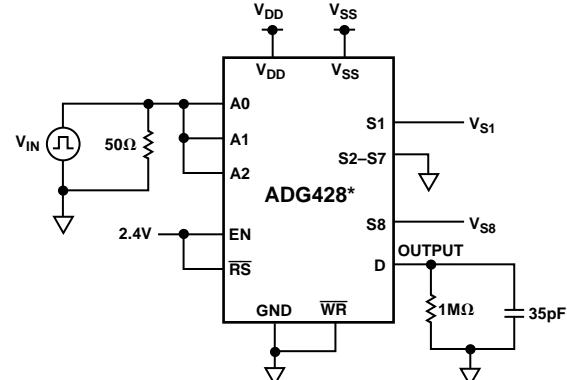
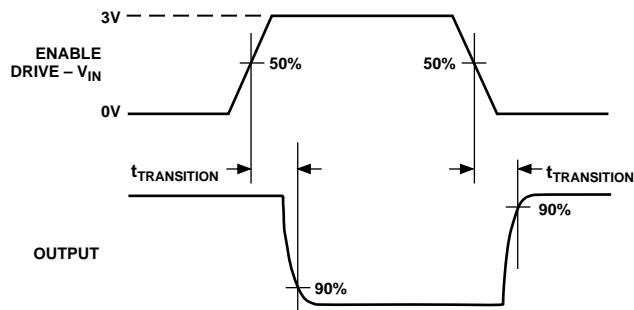
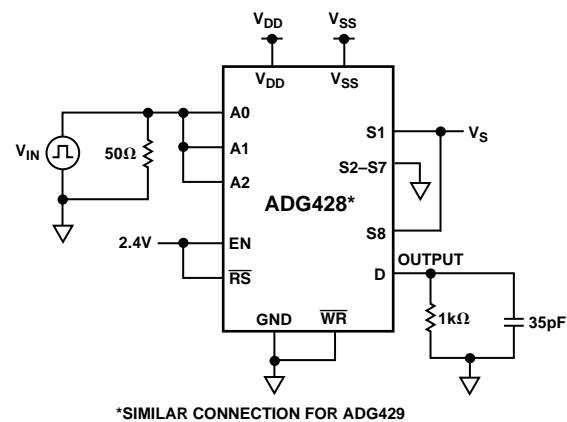
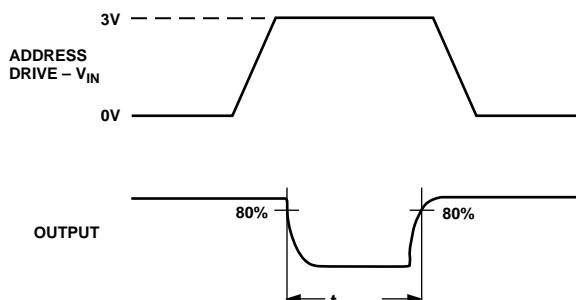
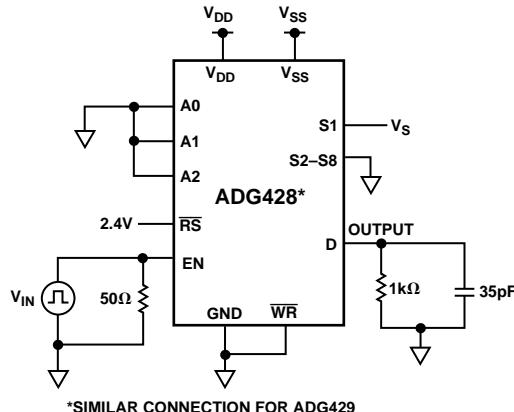
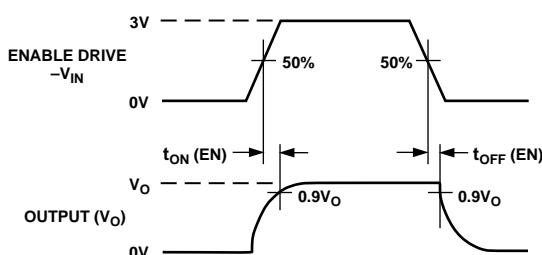


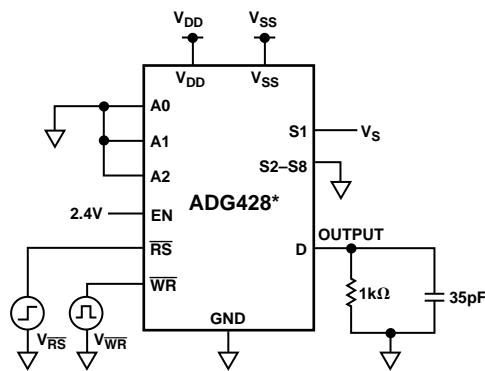
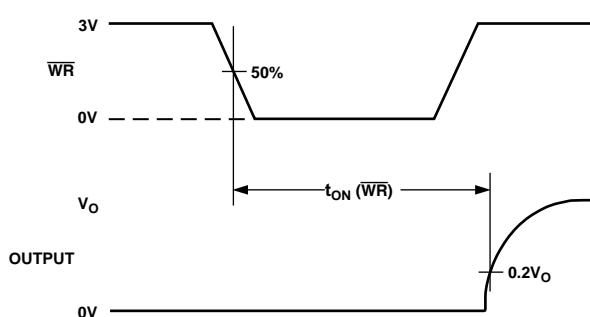
Figure 16. Leakage Currents as a Function of V_D (V_S)

TEST CIRCUITS

Test Circuit 1. On Resistance

Test Circuit 3. I_D (OFF)

Test Circuit 2. I_S (OFF)

Test Circuit 4. I_D (ON)

Test Circuit 5. Switching Time of Multiplexer, $t_{\text{TRANSITION}}$

Test Circuit 6. Break-Before-Make Delay, t_{OPEN}

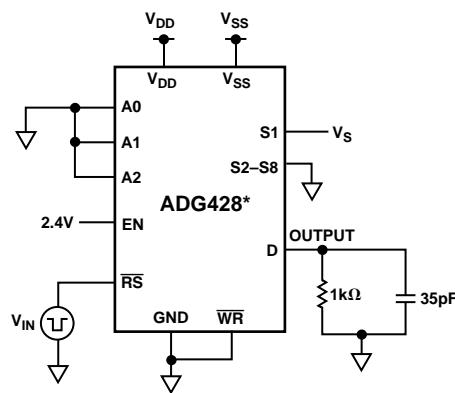
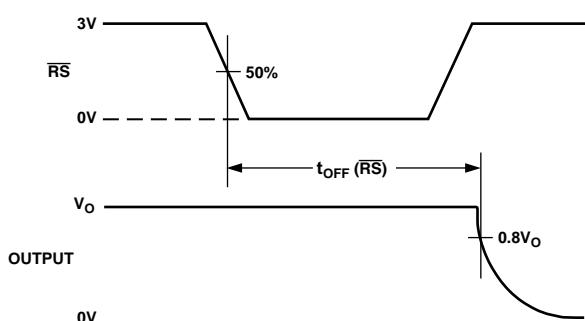
ADG428/ADG429



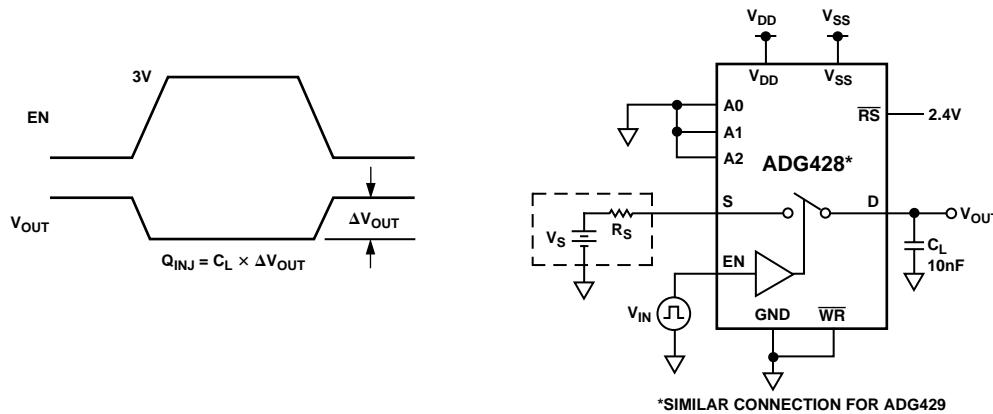
Test Circuit 7. Enable Delay, $t_{ON} (EN)$, $t_{OFF} (EN)$



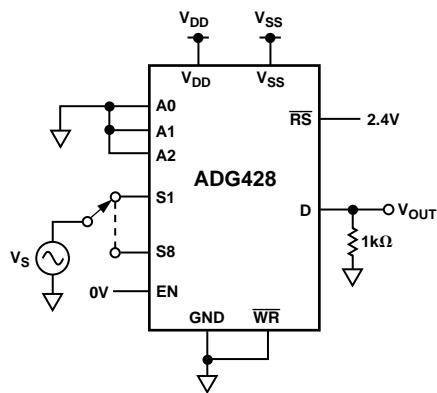
Test Circuit 8. Write Turn-On Time, $t_{ON} (\overline{WR})$



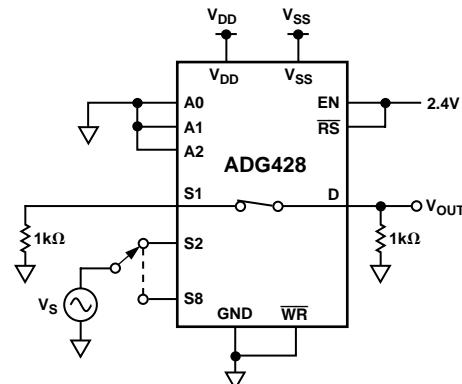
Test Circuit 9. Reset Turn-Off Time, $t_{OFF} (\overline{RS})$



Test Circuit 10. Charge Injection



Test Circuit 11. OFF Isolation



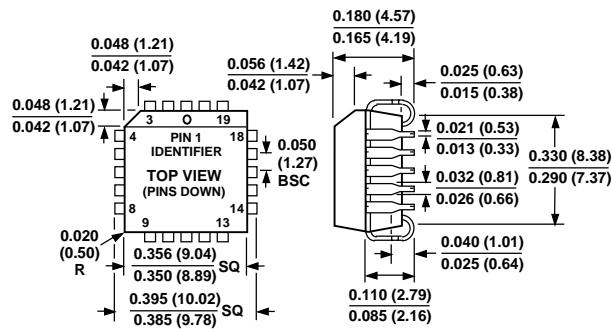
Test Circuit 12. Crosstalk

ADG428/ADG429

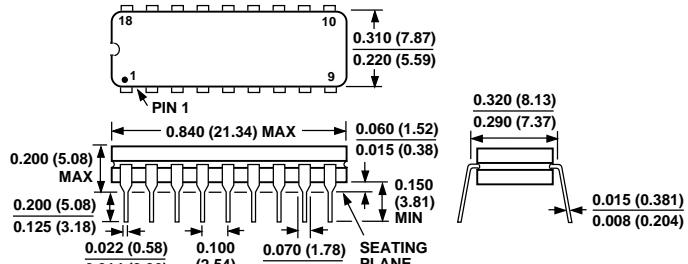
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

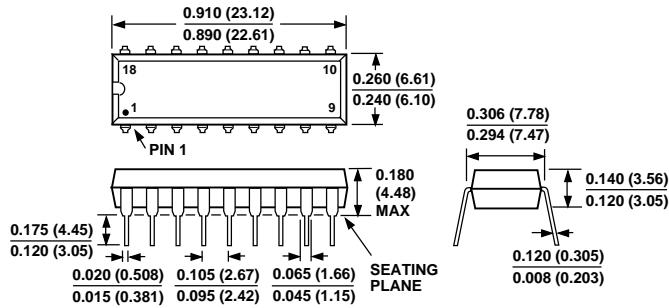
PLCC (P-20A)



Cerdip (Q-18)



Plastic DIP (N-18)



SOIC (R-18)

